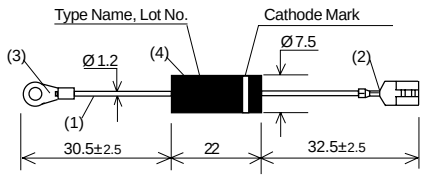
ESJC13 (9kV/450mA,12kV/350mA)

HIGH VOLTEGE DIODE

ESJC13 is high reliability resin molded type high voltage diode in small size package which is sealed a multilayed mesa type silicon chip by epoxy resin.

■ Outline Drawings



No.	Part name	Material and type name
1	Lead wire	Ag plated Cu wire
2	Anode terminal	Flat quick-connect terminal CSS-66325-F (NITIFU TERMINAL INDUSTRIES Co.,LTD) or Equrvalent
3	Cathode terminal	Crimp-type terminal lugs for copper conductor 1.25-4M
4	Molding resin	Epoxy resin UL94V-0

■ Features

- Low V_F
- High Surge proof resistivity
- High reliability .

■ Applications

- Rectification for Microwave oven high voltage power supply

■ Cathode Mark

Type	Mark
ESJA13-09B	■■ ■■ ■■
ESJA13-12B	◆◆ ◆◆ ◆◆

■ Maximum Ratings and Characteristics

- Absolute Maximum Ratings

Items	Symbols	Conditions	ESJC13		Units
			-09B	-12B	
Repetitive Peak Reverse Voltage	V_{RRM}		9	12	kV
Average Forward Current	Io	50HzSine half-wave average value. Ta≦60°C*	450	350	mA
Non-repetitive Peak Reverse Current	I_{RSM}	Wp=1mS.Rectangular-wave. One-shot.Ta=25°C	100		mA
Non-repetitive Peak Forward Current	I_{FSM}	50HzSine half-wave peak value.One-shot.Ta=25°C	30		A
Allowable Junction Temperature	T_j		130		°C
Storage Temperature Range	T_g		-40 to +130		°C

* Cooling Requiremennt:Cathode terminalb is fastened to radiatingfin
That size is more than 50mm•~50mm•~0.6mmt Wind-cooled velocity is more than0.5m/s.

- Electrical Characteristics (Ta=25°C Unless otherwise specified)

Items	Symbols	Conditions	ESJC13		Units
			-09B	-12B	
Maximum Forward Voltage Drop	V_F	I_F=350mA	8	10	V
Maximum Reverse Current	I_R	V_R=12kV	5		μA
Minimum Avalanche Breakdown Voltase	Vz	Iz=100μA	9.5	12.5	kV

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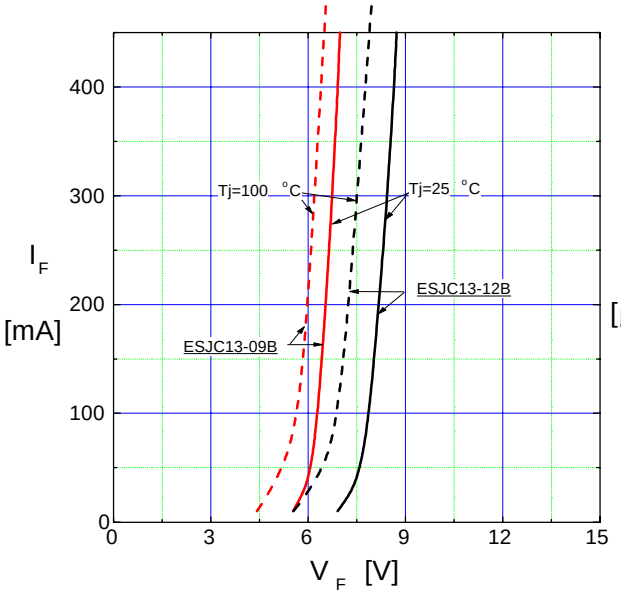
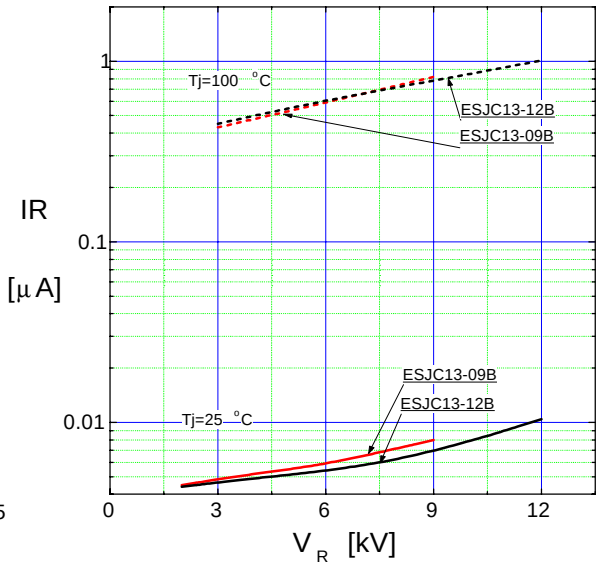
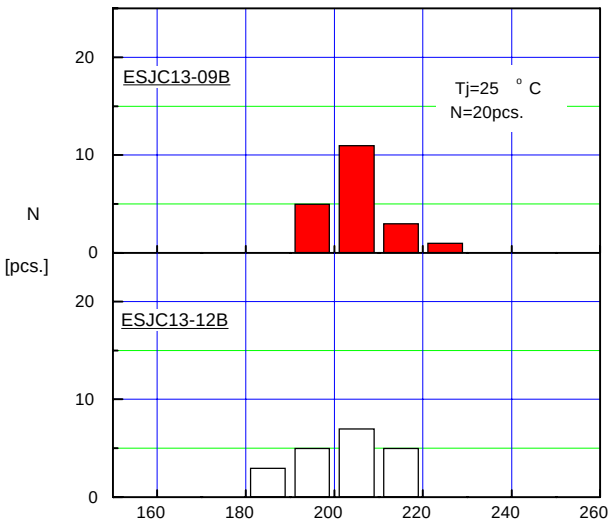
■ Characteristics



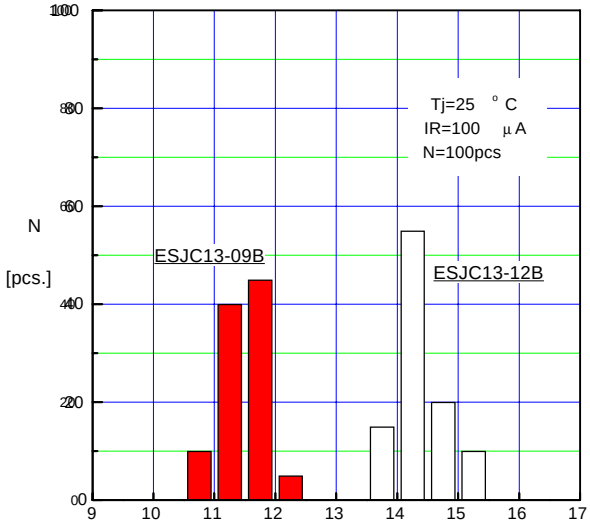
Forward Characteristics



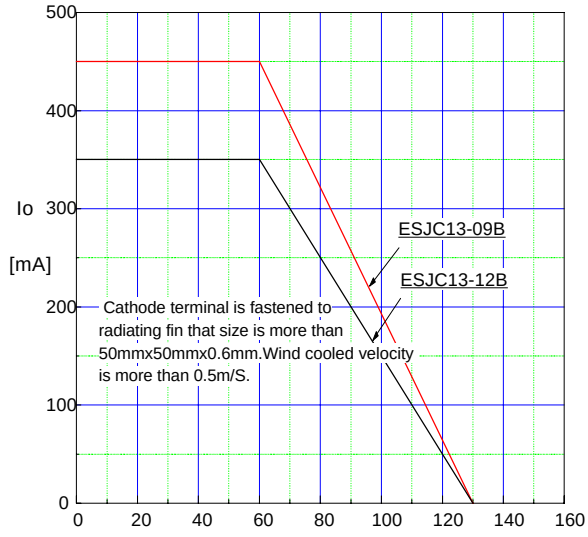
Reverse Characteristics



Reverse Surge Current



Avalanche Breakdown Voltage



Current Derating Curve